

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	388	(117/8).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/10/11 12:12
L2	368	(257/64).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/10/11 12:12
L3	233	(257/75).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/10/11 12:12
L4	370	(117/904).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/10/11 12:12
L5	1177	(438/166).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/11 12:13
L6	158	(257/70).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/11 12:13
L7	339	(257/E29.003).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2006/10/11 12:14
L8	426	polycrystalline and grain near2 (boundary boundaries) and (crystal grain) near2 grow\$3 same amorphous and laser same mask	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/11 12:14
L9	0	(polycrystalline and grain near2 (boundary boundaries) and (crystal grain) near2 grow\$3 same amorphous and laser same mask).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/11 12:14
L10	1557	polycrystalline near2 film and grain near2 (boundary boundaries) and grain near2 (size area diameter)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/11 12:16
L11	1076	L10 and (transistor TFT)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/11 12:14
L12	17	(polycrystalline near2 film and grain near2 (boundary boundaries) and grain near2 (size area diameter)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/11 12:16